

SILICON ABRUPT VARACTOR DIODE

DESCRIPTION:

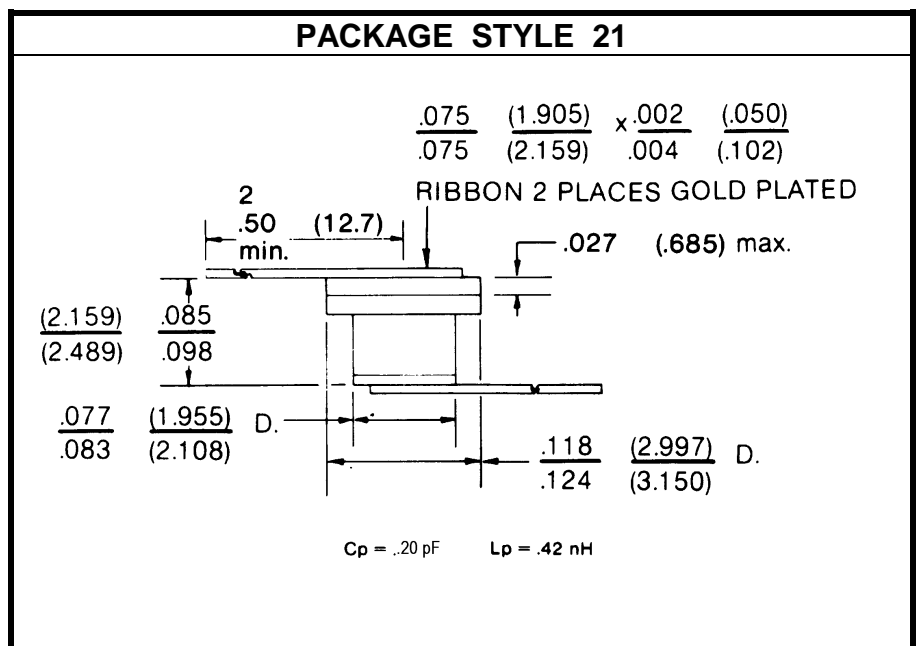
The **AT12016-21** is Designed for High Performance RF and Microwave Applications Requiring an Abrupt Variable Capacitance Characteristic.

FEATURES INCLUDE:

- High Tuning Ratio, $\Delta C_T = 9.0$ MIN.
- High Quality Factor, $Q = 300$ MIN.
- Hermetic Pkg, $C_p = .20$ pF
 $L_s = .42$ nH

MAXIMUM RATINGS

I_F	200 mA
V_R	120 V
P_{DISS}	1.75W @ T_C 25 °C
T_J	-55 °C to +150 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	70 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
V_R	$I_R = 10$ μ A	120			V
V_F	$I_F = 1$ mA			1.0	V
I_R	$V_R = 100$ V			100	μ A
C_T	$V_R = 4$ V $f = 1.0$ MHz	16	18	20	pF
ΔC_T	C_{T0} / C_{T120} $f = 1.0$ MHz	9.0			---
Q	$V_R = 4$ V $f = 50$ MHz	300			---
R_s	$I_F = 10$ mA $f = 2400$ MHz			0.9	Ω